

2018 IEEE BiCMOS and Compound Semiconductor Integrated Circuits and Technology (BCICTS 2018)

**San Diego, California, USA
15-17 October 2018**



**IEEE Catalog Number: CFP18N20-POD
ISBN: 978-1-5386-6503-9**

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|-------------------------|-------------------|
| IEEE Catalog Number: | CFP18N20-POD |
| ISBN (Print-On-Demand): | 978-1-5386-6503-9 |
| ISBN (Online): | 978-1-5386-6502-2 |

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